



MARRI LAXMAN REDDY INSTITUTE OF TECHNOLOGY AND MANAGEMENT

(AN AUTONOMOUS INSTITUTION)

(Approved by AICTE, New Delhi & Affiliated to JNTUH, Hyderabad)

Accredited by NBA and NAAC with 'A' Grade & Recognized Under Section 2(f) & 12(B) of the UGC act, 1956

II B.Tech I Sem Supplementary Examination, February-2022 Electronic Devices and Circuits (ECE)

Time: 3 Hours.

Max. Marks: 70

Note: 1. Answer any FIVE questions.

2. Each question carries 14 marks and may have a, b as sub questions.

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|---|----|--|-----|-----|-----|
| 1 | a) | With necessary waveforms, explain the operation of bridge rectifier. | 7M | C01 | BL4 |
| | b) | A sinusoidal voltage whose $V_m=26V$ is applied to half-wave rectifier. The diode may be considered to be ideal and $R_L=1.2 K\Omega$ is connected as load. Find out peak value of current, RMS value of Current, DC value of current and Ripple factor. | 7M | C01 | BL3 |
| 2 | a) | Derive the expression for diffusion capacitance. | 7M | C01 | BL6 |
| | b) | Sketch the piecewise linear characteristics of a diode. What are the approximate cut-in voltages for silicon and germanium? | 7M | C01 | BL2 |
| 3 | a) | Draw the self bias circuit and derive the stability factor for it along with explanation. | 7M | C02 | BL6 |
| | b) | Calculate the α_{dc} and β_{dc} for the given transistor for which $I_C=5mA$, $I_B=50\mu A$ and $I_{CO} = 1\mu A$. | 7M | C02 | BL3 |
| 4 | a) | Tabulate the comparison of CB, CE and CC configuration with examples. | 7M | C02 | BL2 |
| | b) | An NPN transistor if $\beta=50$ is used in common emitter circuit with $V_{CC}=10V$ and $R_C=2 k\Omega$. The bias is obtained by connecting $100 k\Omega$ resistor from collector to base. Find the quiescent point and stability factor. | 7M | C02 | BL3 |
| 5 | a) | Draw the circuit diagram of SCR and explain its operation along with its characteristics. | 7M | C03 | BL1 |
| | b) | Define and explain the parameters trans-conductance g_m . Drain resistance r_d and amplification factor μ of a JFET. Establish a relation between them. | 7M | C03 | BL4 |
| 6 | a) | Explain the operation of FET. Derive an expression for pinch off voltage of a FET. | 7M | C03 | BL4 |
| | b) | What is tunneling phenomena? Explain the principle of operation of tunnel diode with its characteristics. | 7M | C03 | BL4 |
| 7 | a) | Draw the Common emitter amplifier with Emitter resistor and explain its operation. | 7M | C04 | BL2 |
| | b) | Explain about CC amplifier and derive the expression for h parameters of the same. In addition, derive the expression for gain, input impedance and output impedance of CC amplifier. | 7M | C04 | BL4 |
| 8 | | Briefly discuss about the construction, working and static drain characteristics of enhancement MOSFET? | 14M | C05 | BL2 |